GWM76S60

POWER FIELD EFFECT TRANSISTOR

GENERAL DESCRIPTION

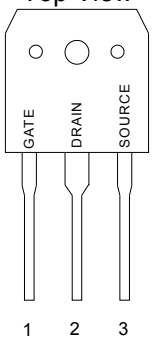
This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

FEATURES

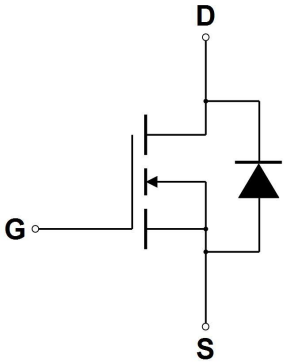
- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and V_{DS}(on) Specified at Elevated Temperature
- Isolated Mounting Hole Reduces Mounting Hardware

PIN CONFIGURATION

TO-247
Top View



SYMBOL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain to Current — Continuous — Pulsed	$I_{D\ (1)}$ I_{DM}	75.3 225.9	A
Gate-to-Source Voltage — Continue	V_{GS}	±20	V
Total Power Dissipation –TO-247 Derate above 25℃ –TO-247	P_D	595 4.76	W W/℃
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	℃
Single Pulse Drain-to-Source Avalanche Energy — T_J = 25℃ (V_{DD} = 100V, V_{GS} = 10V, I_L = 17A, L = 20mH, R_G = 25Ω)	E_{AS}	2890	mJ
Thermal Resistance — Junction to Case -TO-247 — Junction to Ambient -TO-247	θ_{JC} θ_{JA}	0.21 40	℃/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	℃

(1) Drain current limited by maximum junction temperature

ORDERING INFORMATION

Part Number	TOP MARK	Part Number	Packing Mthod	Note
GWM76S60XN247 (Notte1)	GWM76S60X	TO-247	Tube	
GWM76S60GN247 (Notte2)	GWM76S60G	TO-247	Tube	

Note1: X : Suffix for Halogen Free Product,
Note2: G : Suffix for PB Free Product,

ELECTRICAL CHARACTERISTICS

Unless otherwise specified, T_J = 25℃.

			GWM76S60			
Characteristic		**Symbol**	**Min**	**Typ**	**Max**	**Units**
Drain-Source Breakdown Voltage (V_{GS} = 0 V, I_D = 250 μA)		$V_{(BR)DSS}$	600			V
Drain-Source Leakage Current (V_{DS} =600 V, V_{GS} = 0 V)		I_{DSS}			1	uA
Gate-Source Leakage Current-Forward (V_{gsf} = 20 V, V_{DS} = 0 V)		I_{GSSF}			100	nA
Gate-Source Leakage Current-Reverse (V_{gsr} = - 20 V, V_{DS} = 0 V)		I_{GSSR}			100	nA
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μA)		$V_{GS(th)}$	2	3	4	V
Static Drain-Source On-Resistance (V_{GS} = 10 V, I_D = 25.4A) *		$R_{DS(on)}$		36	42	mΩ
Input Capacitance	(V_{DS} =100 V, V_{GS} = 0 V, f = 1.0 MHz)	C_{iss}		6078		pF
Output Capacitance		C_{oss}		247		pF
Reverse Transfer Capacitance		C_{rss}		25		pF
Turn-On Delay Time	(V_{DD} = 300 V, I_D =76 A, R_G = 25Ω) *	$t_{d(on)}$		48.9		ns
Rise Time		t_r		115.2		ns
Turn-Off Delay Time		$t_{d(off)}$		179.9		ns
Fall Time		t_f		113.2		ns
Total Gate Charge	(V_{DS} = 480 V, I_D = 76 A, V_{GS} = 10 V)*	Q_g		143.9		nC
Gate-Source Charge		Q_{gs}		39.5		nC
Gate-Drain Charge		Q_{gd}		60.0		nC
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward On-Voltage(1)	(I_S = 76 A, d_{IS}/d_t = 100A/μs)	V_{SD}			1.5	V
Forward Turn-On Time		t_{on}		**		ns
Reverse Recovery Time		t_{rr}		627		ns

* Pulse Test: Pulse Width ≦300μs, Duty Cycle ≦2%

** Negligible, Dominated by circuit inductance

TYPICAL ELECTRICAL CHARACTERISTICS

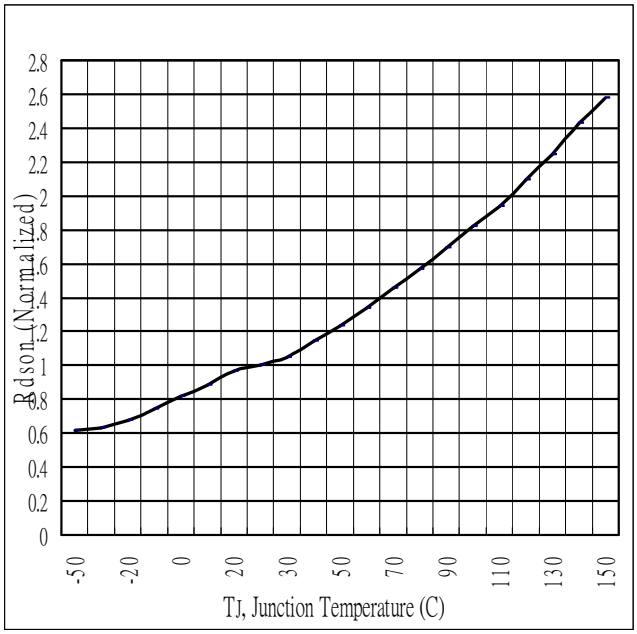


Fig 1. On-Resistance Variation with vs. Temperature

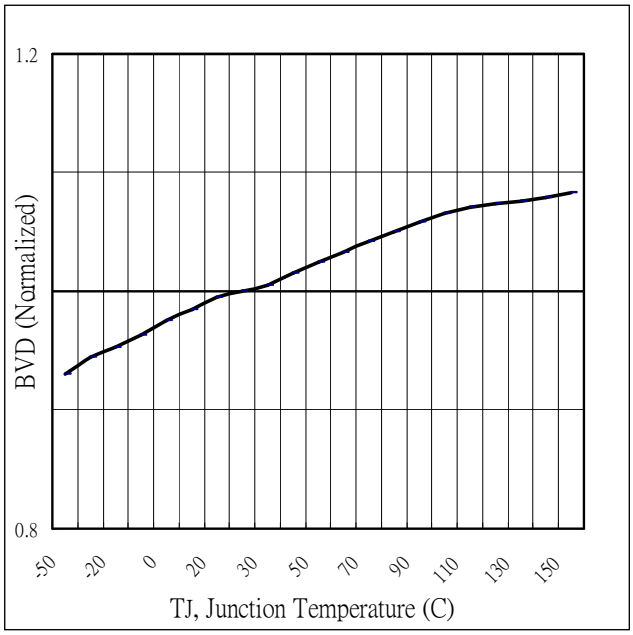


Fig.2 Breakdown Voltage Variation vs. Temperature

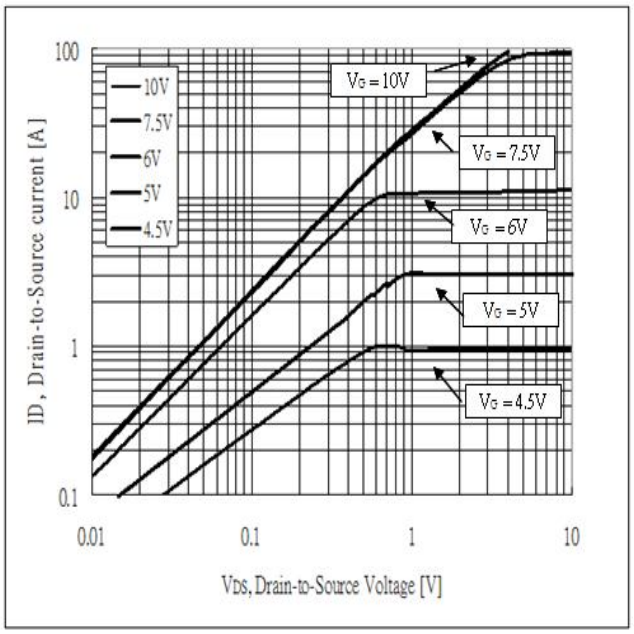


Fig 3. Typical Output Characteristics

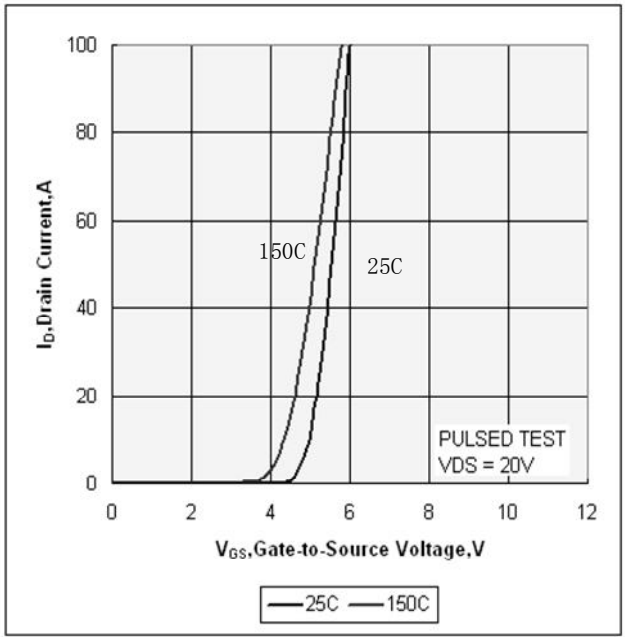


Fig 4. Typical Transfer Characteristics

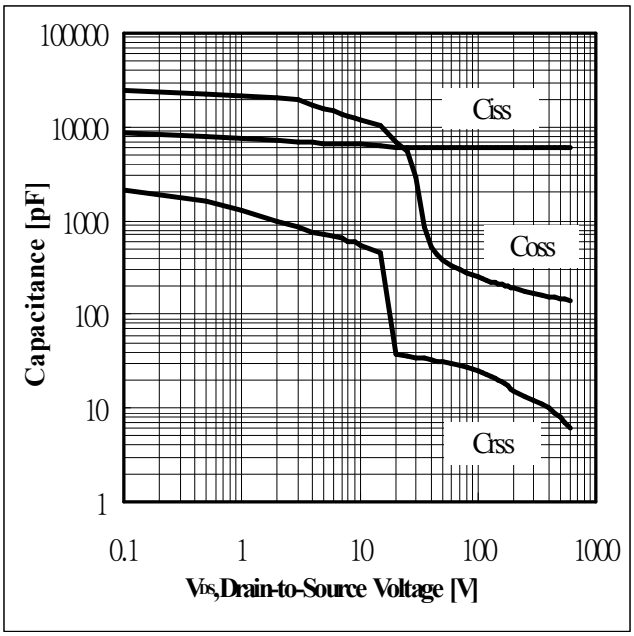


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

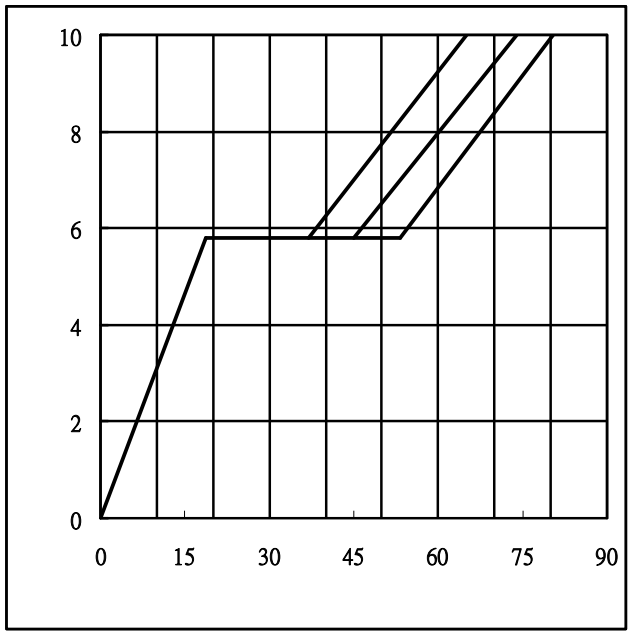


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage